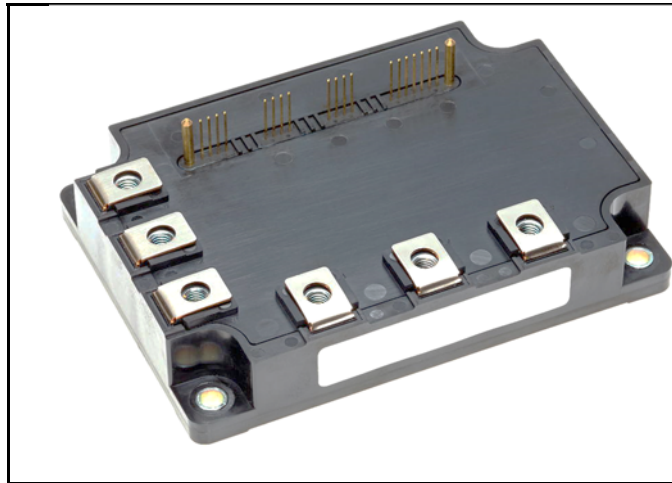


<Intelligent Power Modules>

# PM200RG1C120

FLAT-BASE TYPE  
INSULATED PACKAGE



## FEATURE

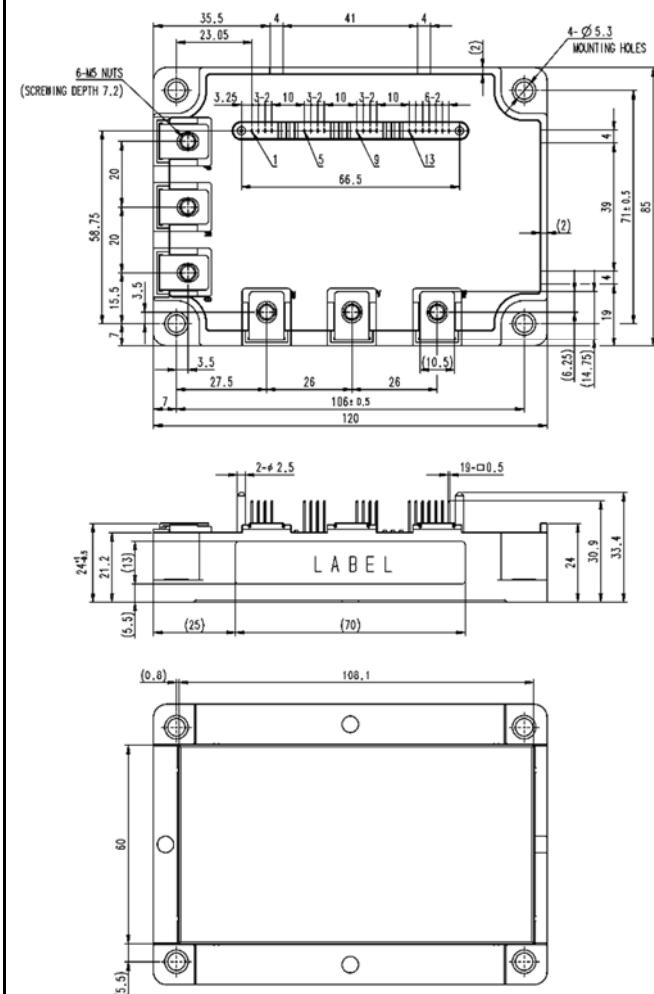
- a) Adopting Full-Gate CSTBT chip.
- b) The over-temperature protection which detects the chip surface temperature of CSTBT is adopted.
- c) Error output signal is available from each protection upper and lower arm of IPM.
- d) Outputting an error signal corresponding to the abnormal state (error mode identification)

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

## APPLICATION

General purpose inverter, servo drives and other motor controls

## PACKAGE OUTLINES



## Dimensions in mm

Tolerance otherwise specified

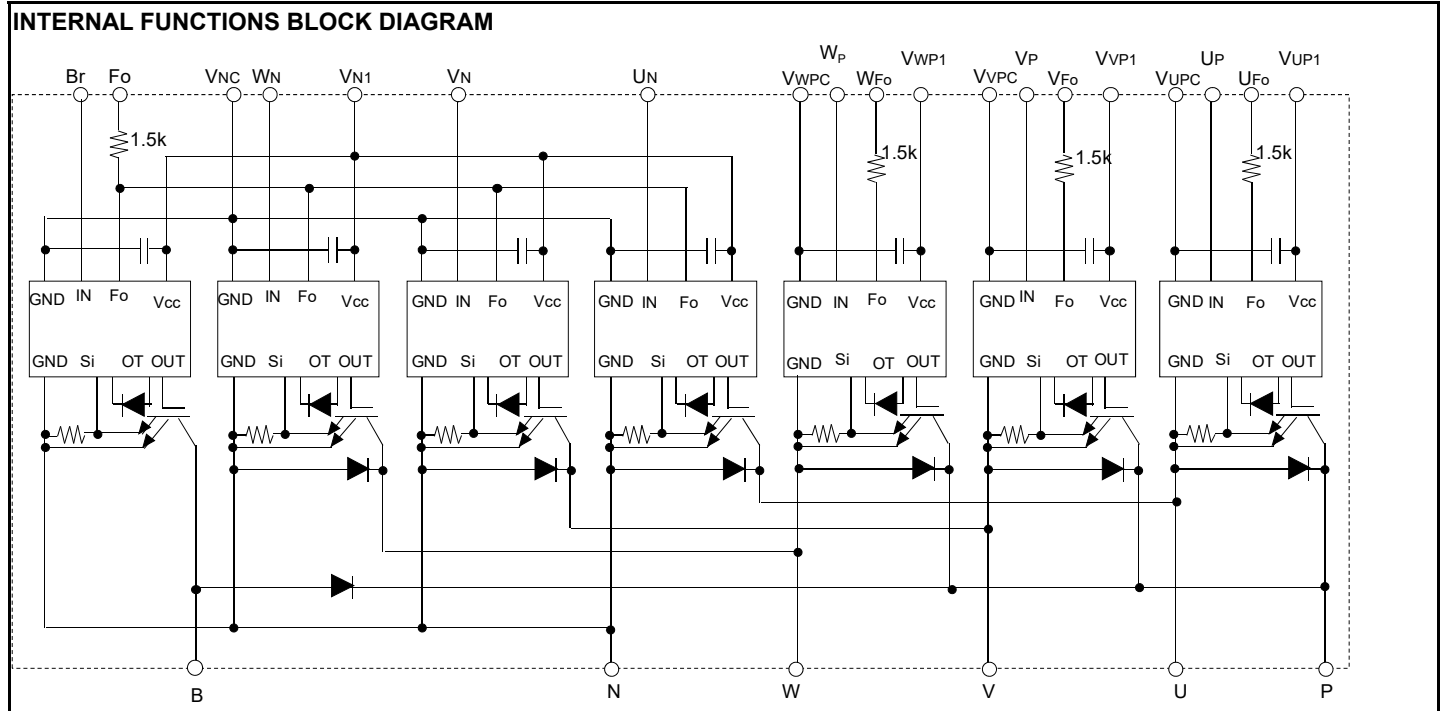
Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

## TERMINAL CODE

- 1.V<sub>UPC</sub>
- 2.U<sub>FO</sub>
- 3.U<sub>P</sub>
- 4.V<sub>UP1</sub>
- 5.V<sub>VP</sub>
- 6.V<sub>FO</sub>
- 7.V<sub>P</sub>
- 8.V<sub>VP1</sub>
- 9.V<sub>WPC</sub>
- 10.W<sub>FO</sub>
- 11.W<sub>P</sub>
- 12.V<sub>WP1</sub>
- 13.V<sub>NC</sub>
- 14.V<sub>N1</sub>
- 15.BR
- 16.U<sub>N</sub>
- 17.V<sub>N</sub>
- 18.W<sub>N</sub>
- 19.Fo

# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE



## MAXIMUM RATINGS (Tvj = 25°C, unless otherwise noted)

### INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CES}$	Collector-Emitter Voltage	$V_D=15\text{ V}, V_{CIN}=15\text{ V}$	1200	V
$I_C$	Collector Current	$T_C=25\text{ }^\circ\text{C}$	200	A
$I_{CRM}$		Pulse	400	
$P_{tot}$	Total Power Dissipation	$T_C=25\text{ }^\circ\text{C}$	1250	W
$I_E$	Emitter Current	$T_C=25\text{ }^\circ\text{C}$	200	A
$I_{ERM}$	(Free-wheeling Diode Forward current)	Pulse	400	
$T_{vj}$	Junction Temperature		-20 ~ +150	°C

\*: Tc measurement point is just under the chip.

### BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CES}$	Collector-Emitter Voltage	$V_D=15\text{ V}, V_{CIN}=15\text{ V}$	1200	V
$I_C$	Collector Current	$T_C=25\text{ }^\circ\text{C}$	100	A
$I_{CRM}$		Pulse	200	
$P_{tot}$	Total Power Dissipation	$T_C=25\text{ }^\circ\text{C}$	735	W
$V_{R(DC)}$	Diode Rated Reverse DC Voltage	$T_C=25\text{ }^\circ\text{C}$	1200	V
$I_F$	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	100	A
$T_{vj}$	Junction Temperature		-20 ~ +150	°C

\*: Tc measurement point is just under the chip.

### CONTROL PART

Symbol	Parameter	Conditions	Ratings	Unit
$V_D$	Supply Voltage	Applied between: $V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC}$	20	V
$V_{CIN}$	Input Voltage	Applied between: $U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N, V_N, W_N, Br -V_{NC}$	20	V
$V_{FO}$	Fault Output Supply Voltage	Applied between: $U_{FO}-V_{UPC}, V_{FO}-V_{VPC}, W_{FO}-V_{WPC}, Fo-V_{NC}$	20	V
$I_{FO}$	Fault Output Current	Sink current at $U_{FO}, V_{FO}, W_{FO}, Fo$ terminals	20	mA

# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE

## TOTAL SYSTEM

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CC(Prot)}$	Supply Voltage Protected by SC	$V_D = 13.5 \text{ V} \sim 16.5 \text{ V}$ , Inverter Part, $T_{vj} = +125^\circ\text{C}$ start	800	V
$T_{stg}$	Storage Temperature	-	-40 ~ +125	$^\circ\text{C}$
$T_C$	Operating Case Temperature	-	-20 ~ +125	$^\circ\text{C}$
$V_{isol}$	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base plate, AC 1min, RMS	2500	V

\*:  $T_C$  measurement point is just under the chip.

## THERMAL RESISTANCE

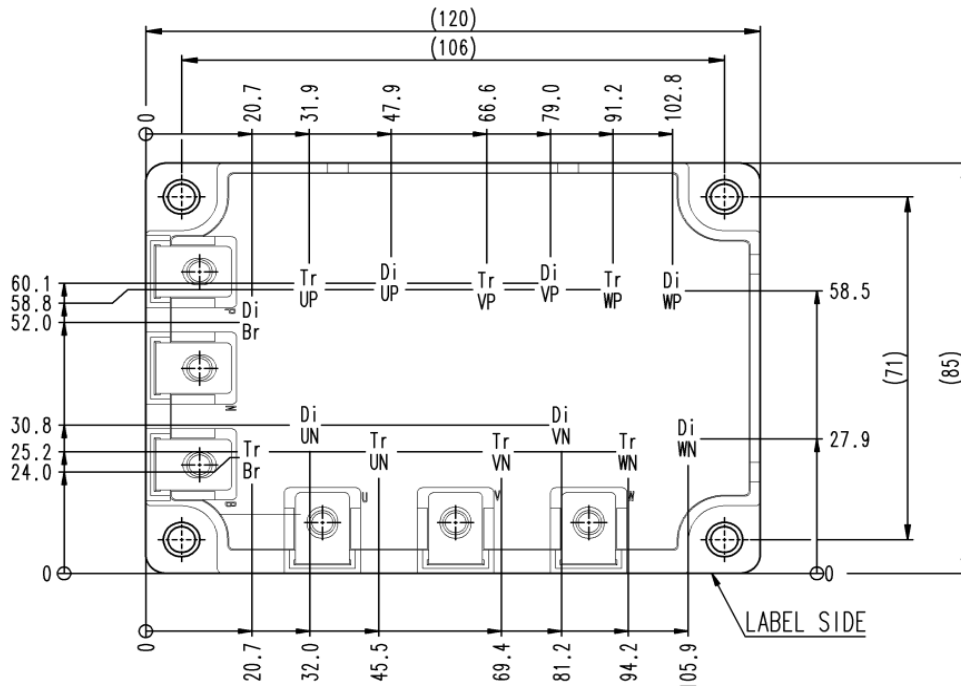
Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal Resistance	Inverter, Junction to case, IGBT, per 1 element (Note1)	-	-	0.10	K/W
$R_{th(j-c)D}$		Inverter, Junction to case, FWD, per 1 element (Note1)	-	-	0.15	
$R_{th(j-c)Q}$		Brake, Junction to case, IGBT, per 1 element (Note1)	-	-	0.17	
$R_{th(j-c)D}$		Brake, Junction to case, FWD, per 1 element (Note1)	-	-	0.25	
$R_{th(c-s)}$	Contact Thermal Resistance	Case to heat sink, per 1 module, Thermal grease applied (Note.1, 2)	-	8.4	-	K/kW

Note1. If you use this value,  $R_{th(s-a)}$  should be measured just under the chips.

Note2. Typical value is measured by using thermally conductive grease of  $\lambda = 0.9 \text{ W}/(\text{m}\cdot\text{K})$ ,  $D_{(c-s)} = 50 \mu\text{m}$ .

### CHIP LOCATION (Top view)

Dimension in mm, tolerance:  $\pm 1 \text{ mm}$



$Tr^{**}$	: IGBT
$Di^{**}$	: FWD

**PM200RG1C120**

HIGH POWER SWITCHING USE

INSULATED TYPE

**ELECTRICAL CHARACTERISTICS** (Tvj= 25°C, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Conditions			Limits			Unit
					Min.	Typ.	Max.	
V <sub>CEsat</sub>	Collector-Emitter Saturation Voltage	V <sub>D</sub> =15 V, I <sub>C</sub> =200 A	Tvj=25 °C	Terminal	-	-	1.95	V
				Chip	-	1.3	-	
		V <sub>CIN</sub> =0 V, Pulsed, (Fig.1)	Tvj=125 °C	Terminal	-	-	2.2	
				Chip	-	1.5	-	
V <sub>EC</sub>	Emitter-Collector Voltage	V <sub>D</sub> =15 V, I <sub>E</sub> =200 A,	Tvj=25 °C	Terminal	-	-	2.45	V
				Chip	-	1.75	-	
		V <sub>CIN</sub> = 15 V, pulsed, (Fig.2)	Tvj=125 °C	Terminal	-	-	2.7	
				Chip	-	1.95	-	
t <sub>on</sub>	Switching Time	V <sub>D</sub> =15 V, V <sub>CIN</sub> =0 V↔15 V, V <sub>CC</sub> =600 V, I <sub>C</sub> =200A, Tvj=125 °C, Inductive Load (Fig.3, 4)			0.3	0.6	1.2	μs
t <sub>rr</sub>					-	0.2	0.4	
t <sub>c(on)</sub>					-	0.2	0.4	
t <sub>off</sub>					-	1.2	2.8	
t <sub>c(off)</sub>					-	0.4	1.2	
I <sub>CES</sub>	Collector-Emitter Cut-off Current	V <sub>CE</sub> =V <sub>CES</sub> , V <sub>D</sub> =15 V, V <sub>CIN</sub> =15 V (Fig.5)		Tvj=25 °C	-	-	1	mA
				Tvj=125 °C	-	-	10	

**BRAKE PART**

Symbol	Parameter	Conditions			Limits			Unit
					Min.	Typ.	Max.	
V <sub>CEsat</sub>	Collector-Emitter Saturation Voltage	V <sub>D</sub> =15 V, I <sub>C</sub> =100A	Tvj=25 °C	Terminal	-	-	1.85	V
				Chip	-	1.3	-	
		V <sub>CIN</sub> =0 V, Pulsed, (Fig.1)	Tvj=125 °C	Terminal	-	-	2.1	
				Chip	-	1.5	-	
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> =100A	Tvj=25 °C	Terminal	-	-	2.4	V
				Chip	-	1.75	-	
			Tvj=125 °C	Terminal	-	-	2.65	
				Chip	-	1.95	-	
I <sub>CES</sub>	Collector-Emitter Cut-off Current	V <sub>CE</sub> =V <sub>CES</sub> , V <sub>D</sub> =15 V, V <sub>CIN</sub> =15 V (Fig.5)		Tvj=25 °C	-	-	1	mA
				Tvj=125 °C	-	-	10	

# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE

## ELECTRICAL CHARACTERISTICS (Tvj = 25°C, unless otherwise noted)

### CONTROL PART

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>D</sub>	Circuit Current	V <sub>D</sub> =15 V, V <sub>CIN</sub> =15 V	V <sub>P1</sub> -V <sub>PC</sub>	-	4	6	mA
			V <sub>N1</sub> -V <sub>NC</sub>	-	16	24	
		V <sub>D</sub> =15 V, V <sub>CIN</sub> =0 V ↔ 15 V, V <sub>CC</sub> =800 V I <sub>C</sub> =0A, Tvj=125 °C, f <sub>C</sub> ≤20kHz	V <sub>P1</sub> -V <sub>PC</sub>	-	54	65	
			V <sub>N1</sub> -V <sub>NC</sub>	-	192	231	
V <sub>th(ON)</sub>	Input ON Threshold Voltage	Applied between:	1.2	1.5	1.8	V	
V <sub>th(OFF)</sub>	Input OFF Threshold Voltage	U <sub>P</sub> -V <sub>UPC</sub> , V <sub>P</sub> -V <sub>VPC</sub> , W <sub>P</sub> -V <sub>WPC</sub> , U <sub>N</sub> , V <sub>N</sub> , W <sub>N</sub> , Br-V <sub>NC</sub>	1.7	2.0	2.3		
SC	Short Circuit Trip Level	-20≤Tvj≤125 °C, V <sub>D</sub> =15 V (Fig.3, 6)	Inverter	400	-	-	A
			Brake	200	-	-	
t <sub>d(SC)</sub>	Short Circuit Current Delay Time	V <sub>D</sub> =15 V, Tvj=125 °C (Fig.3, 6)	-	2.0	-	μs	
OT	Over Temperature Protection	Detect temperature of IGBT chip surface	Trip level	150	-	-	°C
			Hysteresis	-	20	-	
UV <sub>t</sub>	Supply Circuit	-	Trip level	11.0	12.0	12.7	V
UV <sub>r</sub>	Under-Voltage Protection		Reset level	-	12.5	-	
I <sub>FO(H)</sub>	Fault Output Current	V <sub>D</sub> =15 V, V <sub>FO</sub> =15 V (Note3)	-	-	0.01	mA	
I <sub>FO(L)</sub>			-	10	15		
t <sub>FO</sub>	Fault Output Pulse Width	V <sub>D</sub> =15 V (Note3)	OT	-	8.0	-	ms
			UV	-	4.0	-	
			SC	-	2.0	-	

Note3. Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

### MECHANICAL RATINGS AND CHARACTERISTICS

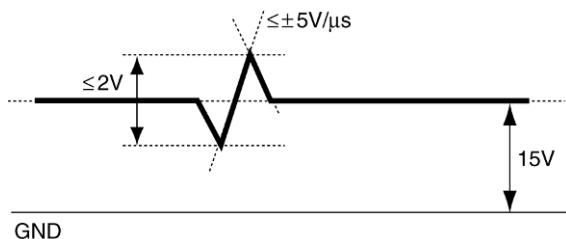
Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M <sub>s</sub>	Mounting Torque	Mounting part screw : M5	2.5	3.0	3.5	N•m
M <sub>t</sub>	Mounting Torque	Main terminal part screw : M5	2.5	3.0	3.5	
m	mass	-	-	425	-	g

### RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Conditions	Recommended value	Unit
V <sub>CC</sub>	Supply Voltage	Applied across P-N terminals	≤ 800	V
V <sub>D</sub>	Control Supply Voltage	Applied between : V <sub>UP1</sub> -V <sub>UPC</sub> , V <sub>VP1</sub> -V <sub>VPC</sub> , V <sub>WP1</sub> -V <sub>WPC</sub> , V <sub>N1</sub> -V <sub>NC</sub> (Note4)	15.0±1.5	V
V <sub>CIN(ON)</sub>	Input ON Voltage	Applied between : U <sub>P</sub> -V <sub>UPC</sub> , V <sub>P</sub> -V <sub>VPC</sub> , W <sub>P</sub> -V <sub>WPC</sub> , U <sub>N</sub> , V <sub>N</sub> , W <sub>N</sub> , Br-V <sub>NC</sub>	≤ 0.8	V
V <sub>CIN(OFF)</sub>	Input OFF Voltage		≥ 9.0	
f <sub>PWM</sub>	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t <sub>dead</sub>	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig.7)	≥ 2.5	μs

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note4. With ripple satisfying the following conditions: dv/dt swing ≤ ±5 V/μs, Variation ≤ 2 V peak to peak



# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE

## PRECAUTIONS FOR TESTING

1. Before applying any control supply voltage ( $V_D$ ), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.

After this, the specified ON and OFF level setting for each input signal should be done.

2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above  $V_{CES}$  rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)

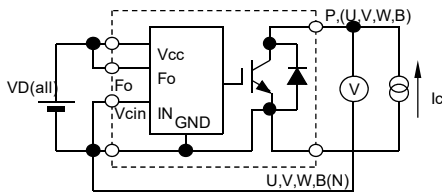


Fig.1  $V_{CESat}$  Test

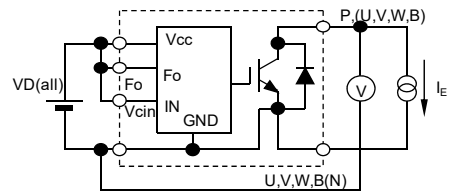


Fig.2  $V_{EC}$  Test

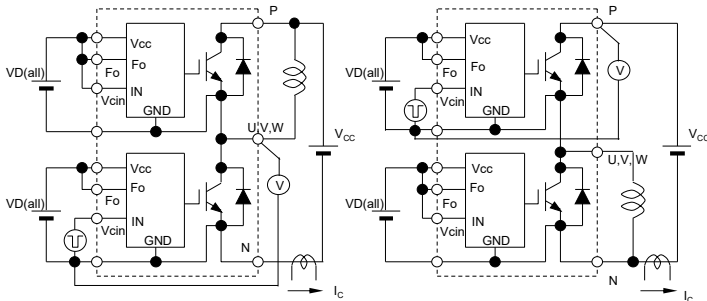


Fig.3 Switching time and SC test circuit

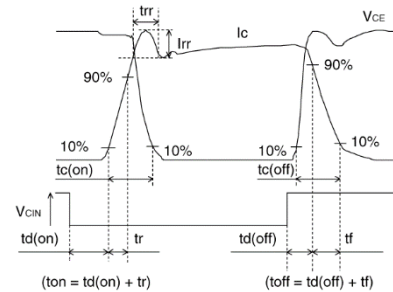


Fig.4 Switching time test waveform

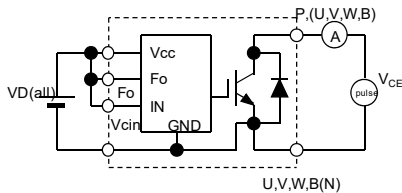


Fig.5  $I_{CES}$  Test

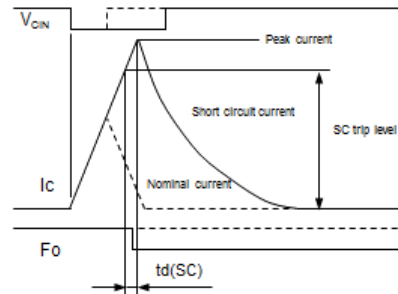
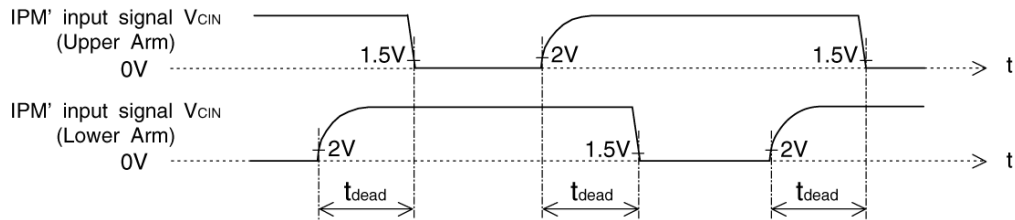


Fig.6 SC test waveform



1.5V: Input on threshold voltage  $V_{th(on)}$  typical value, 2V: Input off threshold voltage  $V_{th(off)}$  typical value

Fig. 7 Dead time measurement point example

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HIGH POWER SWITCHING USE  
INSULATED TYPE

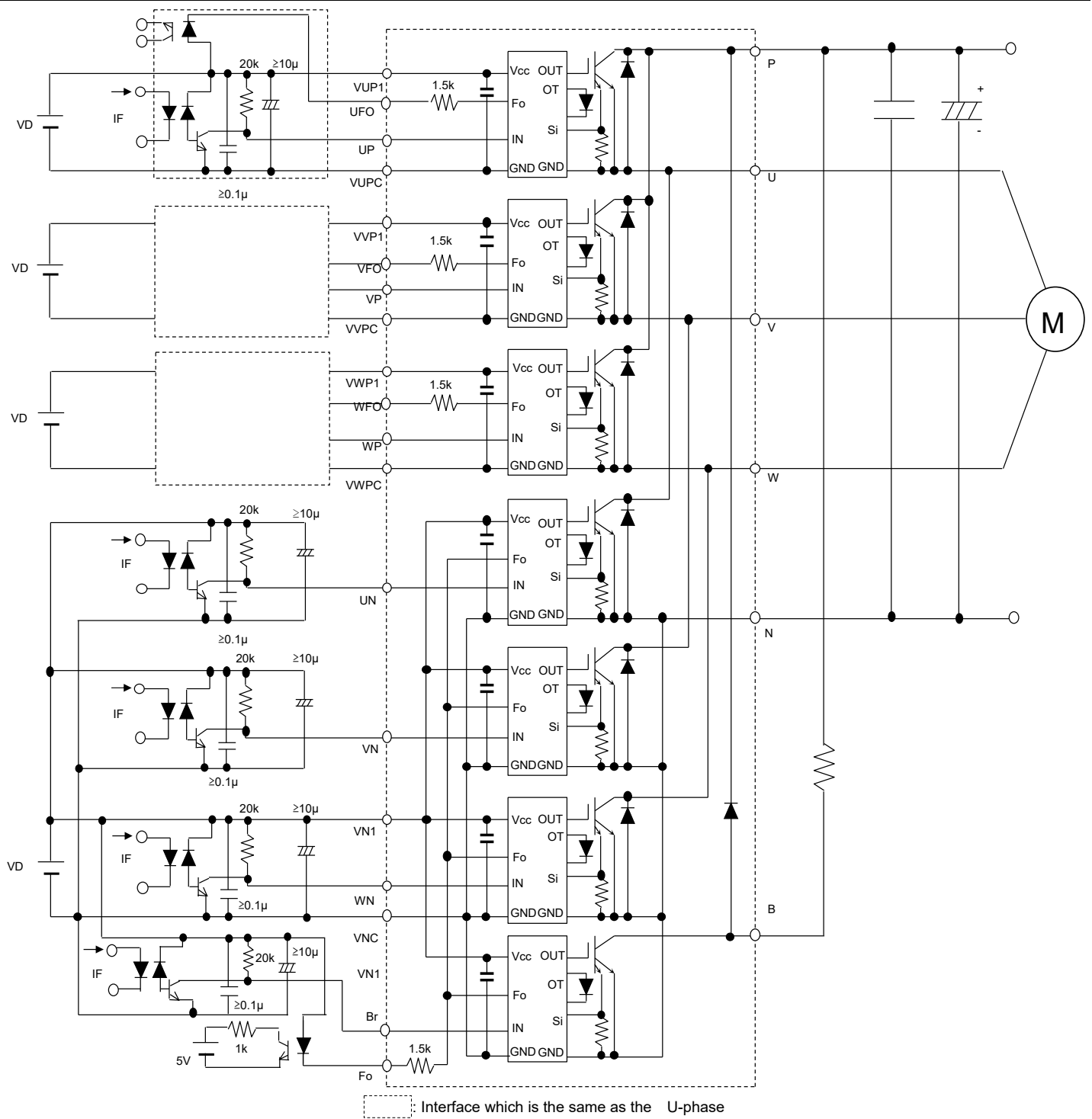


Fig. 8 Application Example Circuit

**NOTES FOR STABLE AND SAFE OPERATION ;**

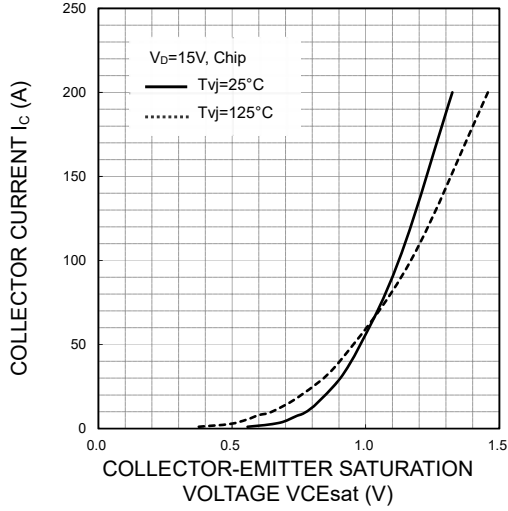
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers:  $t_{PLH}, t_{PHL} \leq 0.8\mu s$ , Use High CMR type.
- Slow switching opto-coupler: CTR > 100% (\*can be applied to Brake part input signal, in this case, resistor should be selected properly).
- Use 4 isolated control power supplies ( $V_D$ ). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.

# PM200RG1C120

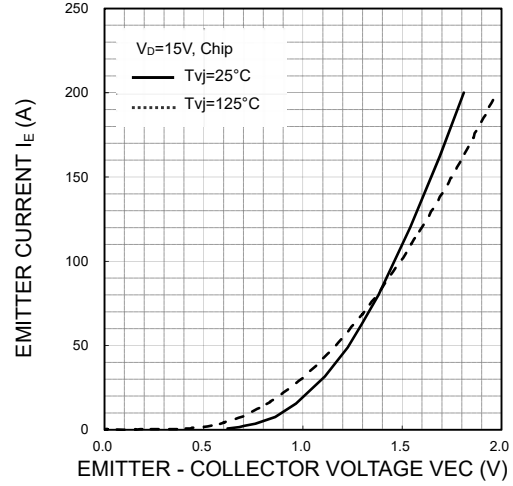
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES Inverter part

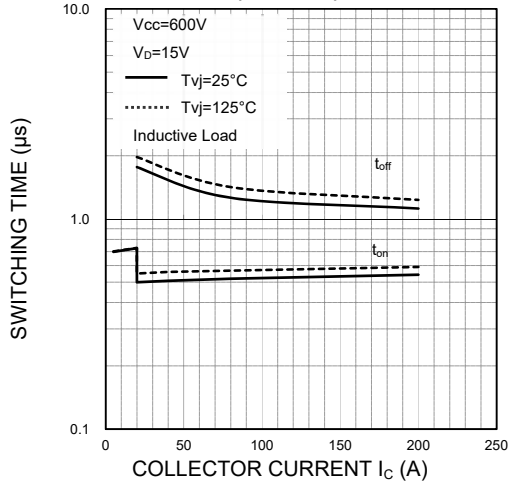
**COLLECTOR-EMITTER SATURATION VOLTAGE (VS.  $I_c$ ) CHARACTERISTICS (TYPICAL)**



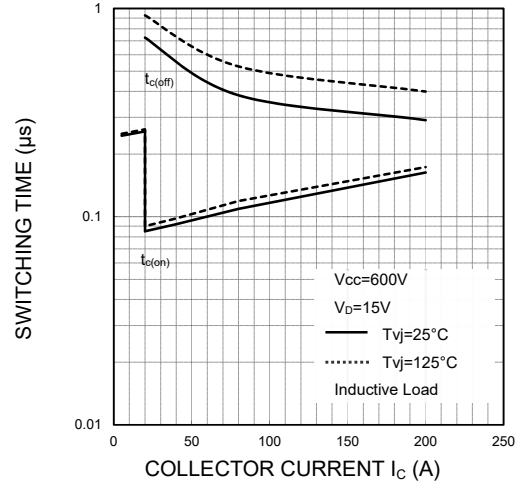
**FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)**



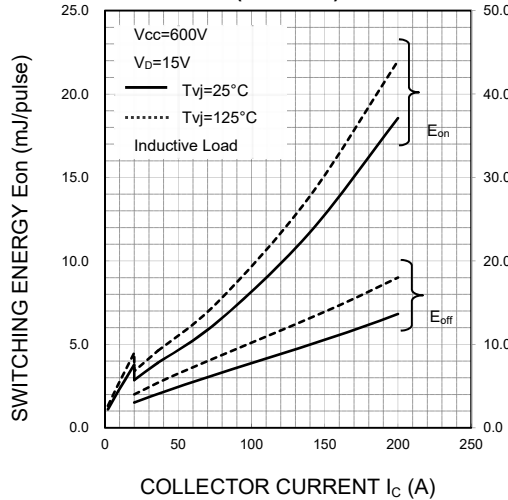
**SWITCHING TIME ( $t_{on}$ ,  $t_{off}$ ) CHARACTERISTICS (TYPICAL)**



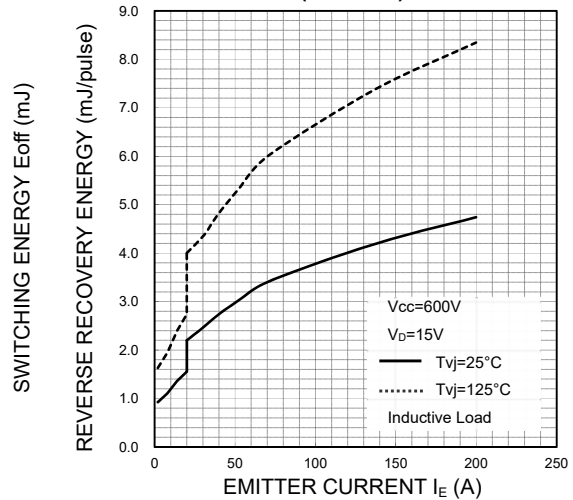
**SWITCHING TIME ( $t_{c(on)}$ ,  $t_{c(off)}$ ) CHARACTERISTICS (TYPICAL)**



**SWITCHING ENERGY  $E_{on}$  CHARACTERISTICS (TYPICAL)**



**FREE WHEELING DIODE REVERSE RECOVERY ENERGY CHARACTERISTICS (TYPICAL)**

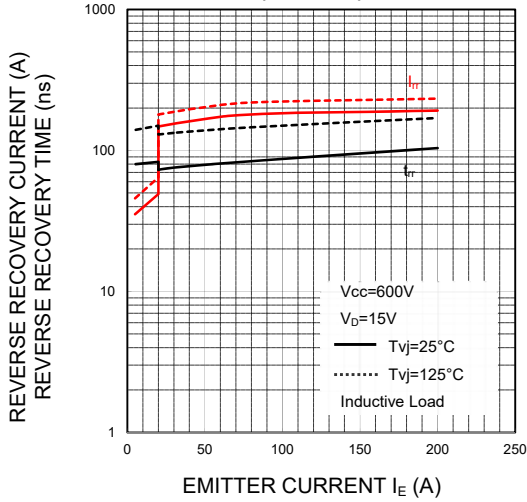




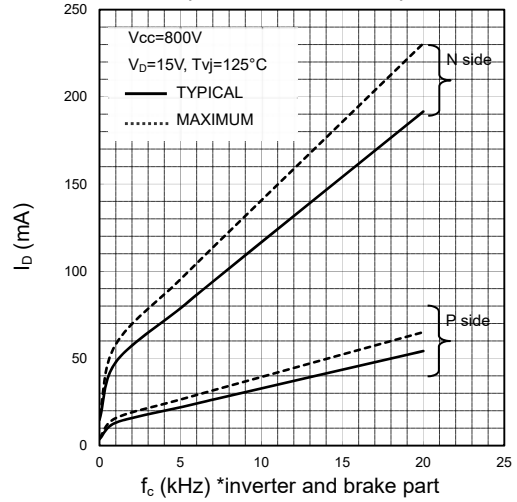
# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE

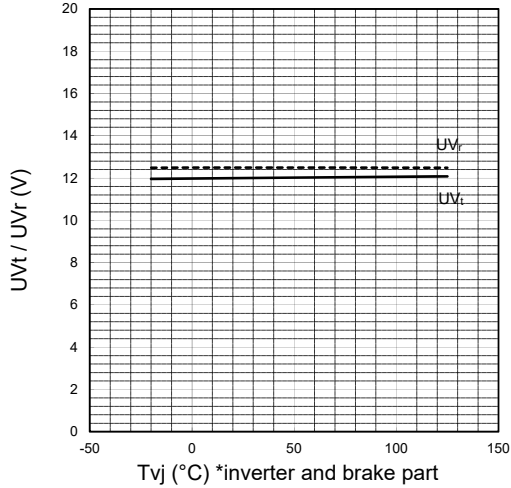
**FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**



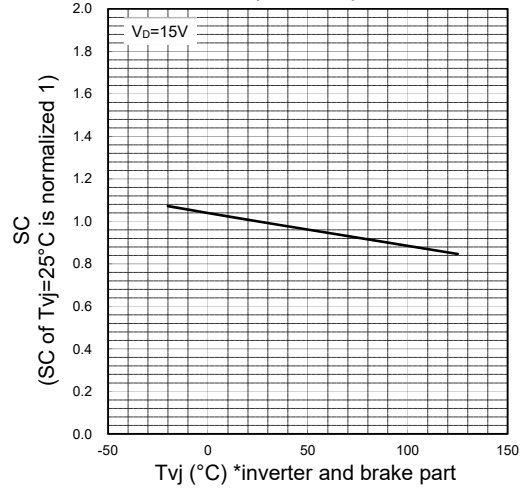
**$I_D$  VS.  $f_c$  CHARACTERISTICS (TYPICAL, MAXIMUM)**



**UV TRIP LEVEL VS.  $T_{vj}$  CHARACTERISTICS (TYPICAL)**

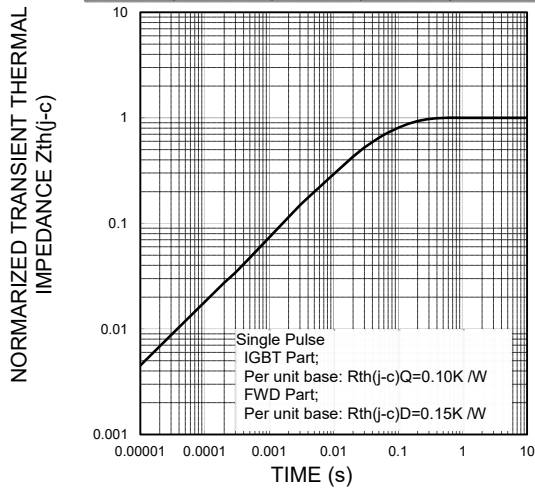


**SC TRIP LEVEL VS.  $T_{vj}$  CHARACTERISTICS (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (TYPICAL)**

i	1	2	3	4
$R_i$	0.0124	0.0739	0.3505	0.5632
$\tau_i$ (s)	1.961E-05	0.0014	0.0179	0.0944



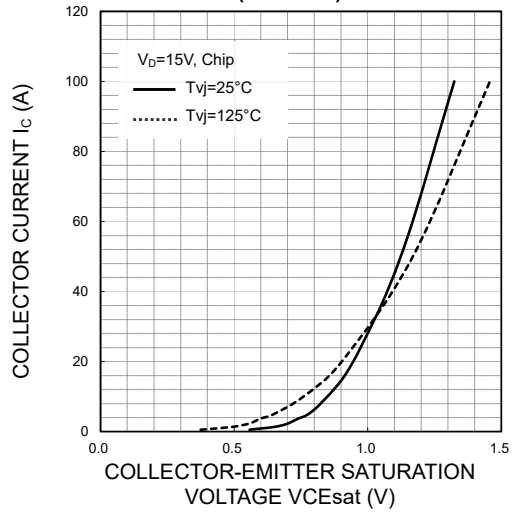
# PM200RG1C120

HIGH POWER SWITCHING USE  
INSULATED TYPE

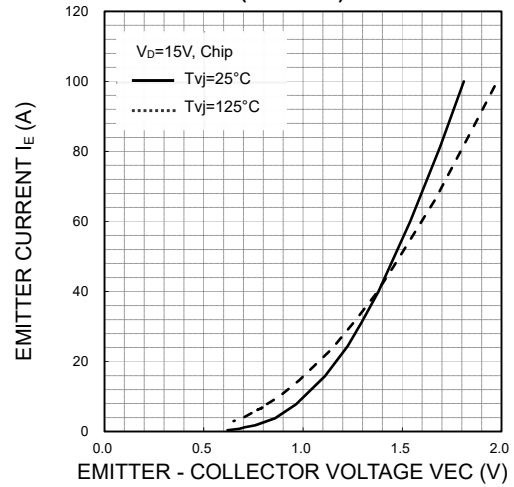
## PERFORMANCE CURVES

Brake part

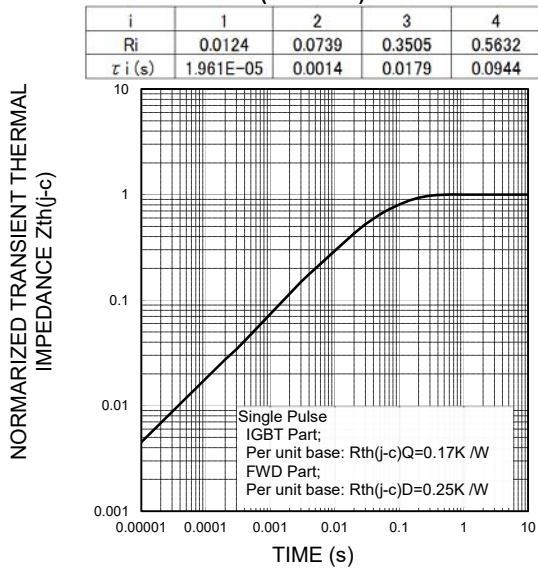
**COLLECTOR-EMITTER SATURATION VOLTAGE (VS.  $I_c$ ) CHARACTERISTICS (TYPICAL)**



**FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (TYPICAL)**



### **Keep safety first in your circuit designs!**

This product is designed for industrial application purpose. The performance, the quality and support level of the product is guaranteed by "Customer's Std. Spec."

Mitsubishi Electric Corporation puts its reasonable effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or to be used under special circumstances (e.g. high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situation which terminal of semiconductor products is received strong mechanical stress).

In the customer's research and development, please evaluate it not only with a single semiconductor product but also in the entire system, and judge whether it's applicable. Furthermore, trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits (e.g. appropriate fuse or circuit breaker between a power supply and semiconductor products), (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

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